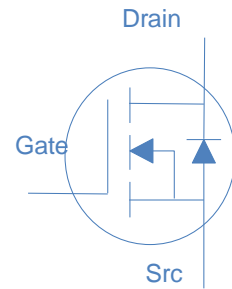




## 100V N-Ch Power MOSFET

$V_{DS}$	100	V
$R_{DS(on),typ}$	3.7	mΩ
$I_D$ (Silicon Limited)	112	A
$I_D$ (Package Limited)	60	A

Fast switching  
 High speed smooth switching  
 Excellent diode dv/dt capability  
 Excellent Ruggedness  
 100% Rg Tested  
 Lead Free  
 Conversion  
 High Speed Circuit



		GNO42N10S

Maximum Ratings at  $T_j=25^\circ\text{C}$  (unless otherwise specified) Part Number HGN042N10S Package TO-18 Marking

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	$I_D$	$T_C=25$	112	A
		$T_C=100$	71	
		$T_C=25$		
Continuous Drain Current (Package Limited)				
	$V_{DS}$	-	100	V
				W
Operating and Storage Temperature	$T_J, T_{Drain}$	to Source Voltage	-55 to 150	

### Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.2	$^{\circ}\text{C/W}$
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	50	$^{\circ}\text{C/W}$

Turn on Delay Time	$t_{d(on)}$		-	14	-	
Rise time		$V_{DD}=50V, I_D=20A, V_{GS}=10V,$ $R_G=10\Omega,$	-	10	-	ns
Fall Time	$t_f$		-	50	-	
			-	15	-	

## Reverse Diode Characteristics

		$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R=50V, I_F=20A, di_F/dt=500A/\mu s$	-	70	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	315	-	nC

Fig 1. Typical Output Characteristics

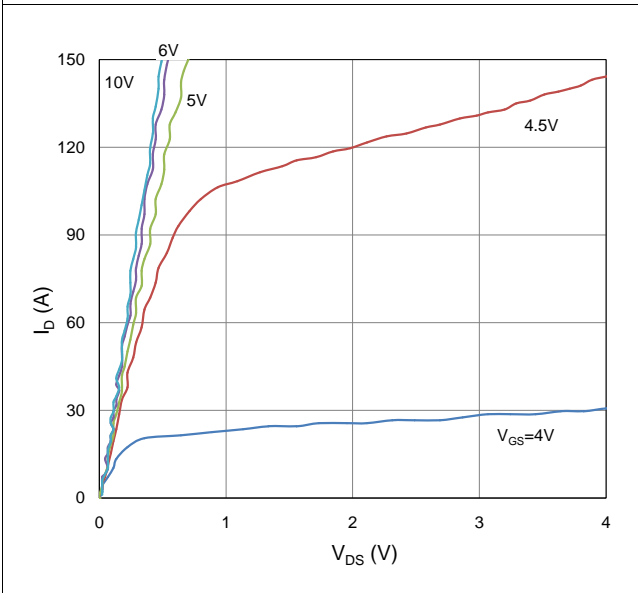


Figure 2. On-Resistance vs. Gate-Source Voltage

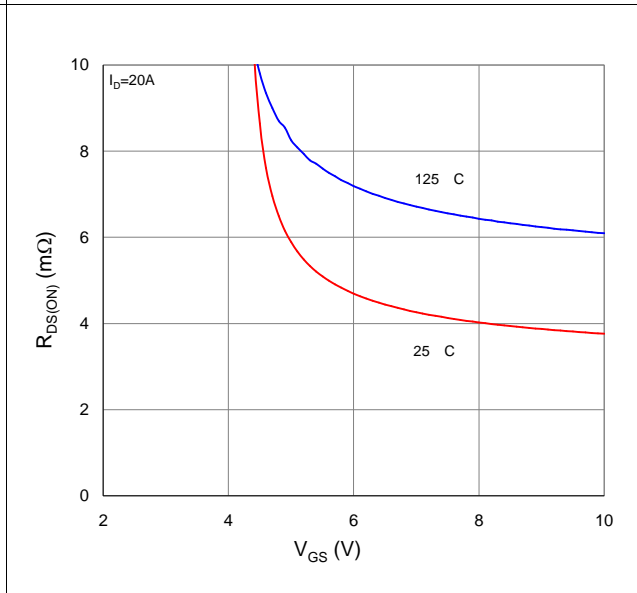


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

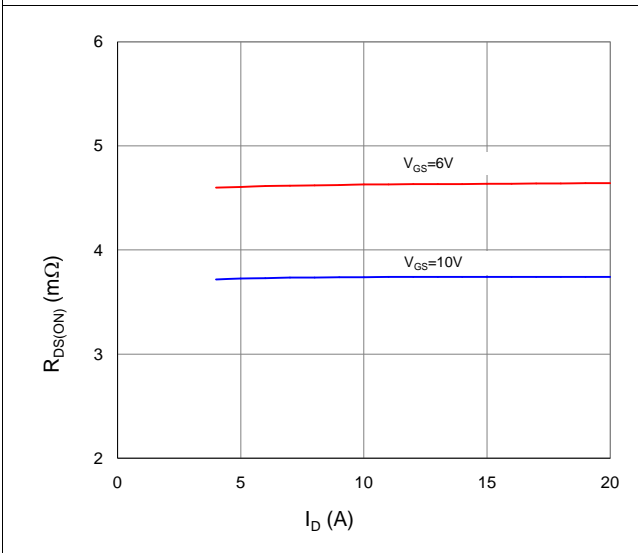


Figure 4. Normalized On-Resistance vs. Junction Temperature

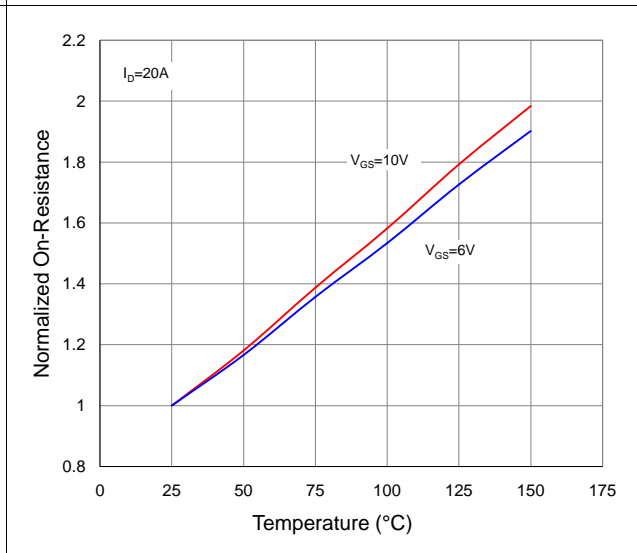


Figure 5. Typical Transfer Characteristics

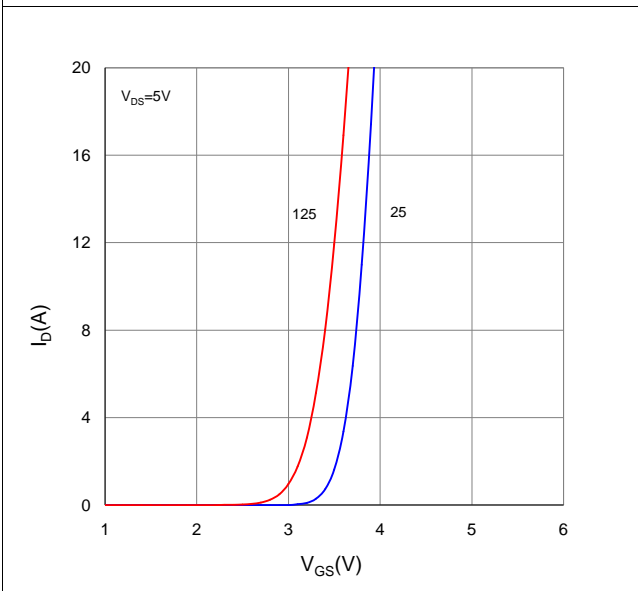


Figure 6. Typical Source-Drain Diode Forward Voltage

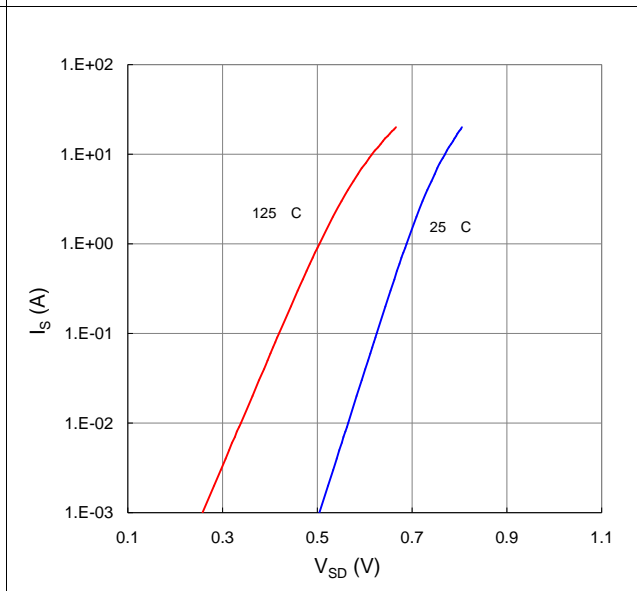


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

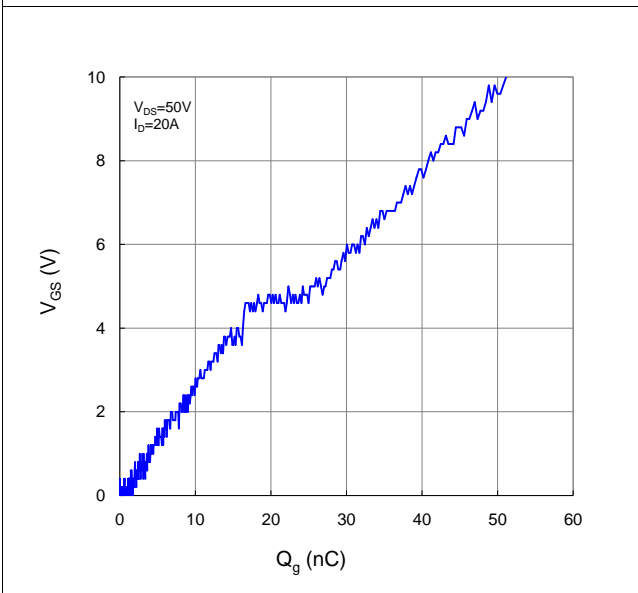


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

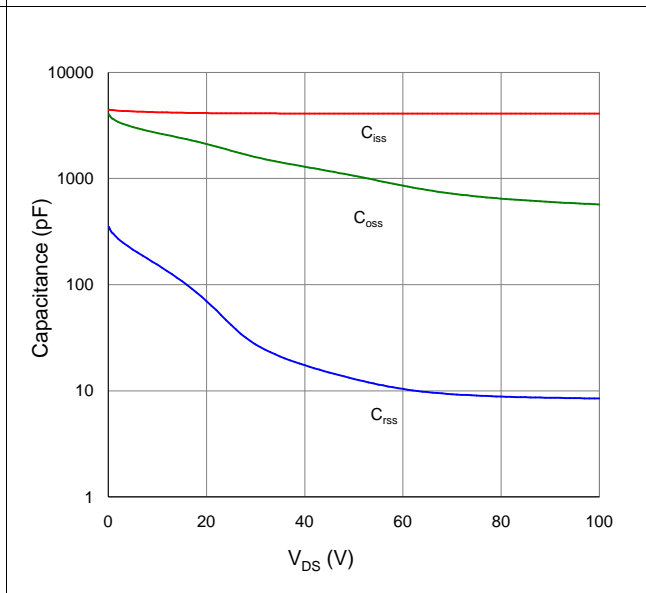


Figure 9. Maximum Safe Operating Area

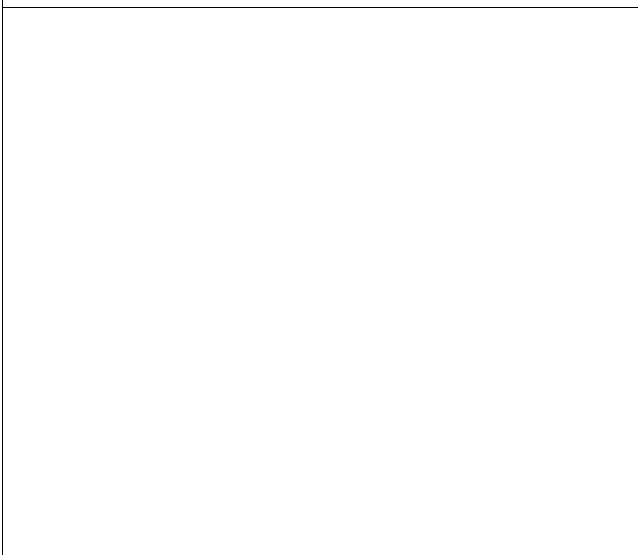


Figure 10. Maximun Drain Current vs. Case Temperature

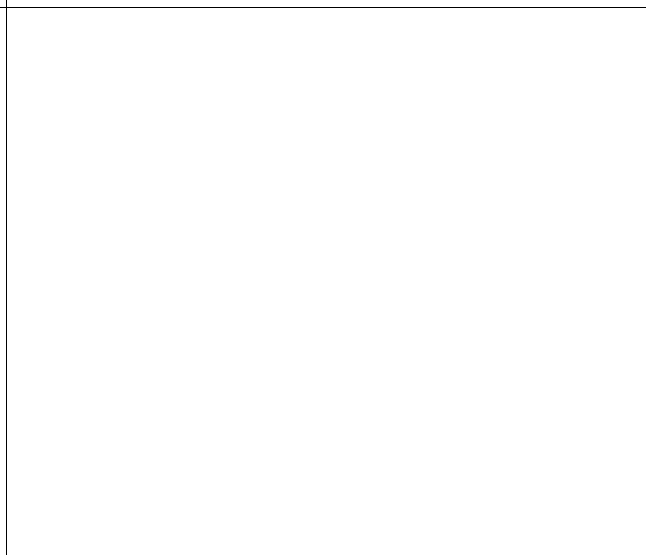
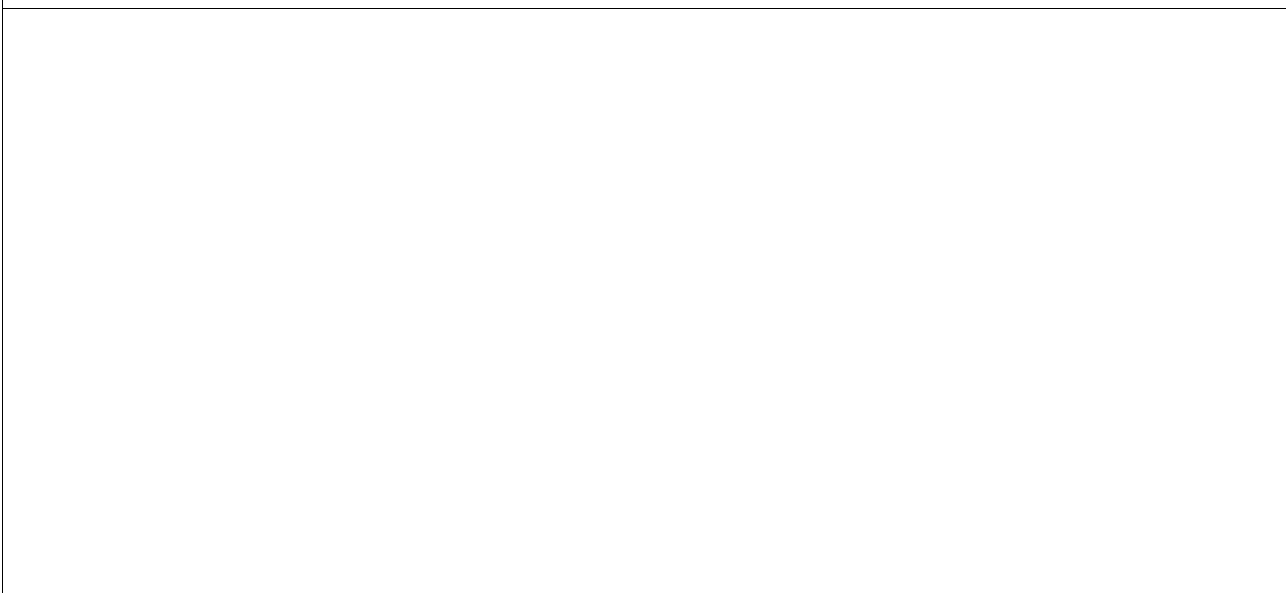


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case





## Package Outline

### DFN5x6\_P, 8 Leads

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A3	0.254 REF		0.010REF	
D	4.680	5.120	0.184	0.202
E	5.900	6.126	0.232	0.241
D1	3.610	4.110	0.142	0.162
E1	3.380	3.780	0.133	0.149
D2	4.800	5.000	0.189	0.197
E2	5.674	5.826	0.223	0.229
k	1.100	1.390	0.043	0.055
b	0.330	0.510	0.013	0.020
e	1.270TYP		1.270TYP	
L	0.510	0.711	0.020	0.028
L1	0.424	0.576	0.017	0.023
H	0.410	0.726	0.016	0.029
θ	0°	12°	0°	12°